

RGTH50TK65

650V 25A Field Stop Trench IGBT

V _{CES}	650V
I _{C(100°C)}	16A
V _{CE(sat) (Typ.)}	1.6V@I _C =25A
P_D	59W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

Applications

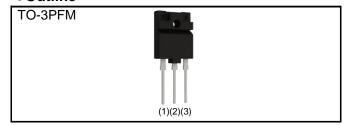
PFC

UPS

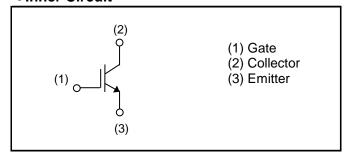
Power Conditioner

ΙH

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTH50TK65

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	26	А
	T _C = 100°C	I _C	16	А
Pulsed Collector Current		I _{CP} *1	100	А
Power Dissipation	T _C = 25°C	P_{D}	59	W
	T _C = 100°C	P_{D}	29	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{jmax.}

●Thermal Resistance

Doromotor	Symbol	Values			Unit
Parameter		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	2.51	°C/W

ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
- Farameter Sy		Conditions	Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	1	-	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 650V, V_{GE} = 0V$	-	-	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, \ V_{CE} = 0V$		-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 17.5 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage		$I_C = 25A, V_{GE} = 15V$				
	V _{CE(sat)}	$T_j = 25$ °C $T_j = 175$ °C	-	1.6	2.1	V
		T _j = 175°C	-	2.1	-	

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
Farameter			Min.	Тур.	Max.	Uniii
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1410	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	57	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	22	-	
Total Gate Charge	Q _g	V _{CE} = 300V	-	49	-	
Gate - Emitter Charge	Q_{ge}	I _C = 25A	-	15	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	19	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 25A, V_{CC} = 400V$	-	27	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	38	-	no
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	94	-	ns
Fall Time	t _f	Inductive Load	-	50	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 25A, V_{CC} = 400V$	-	27	-	
Rise Time	t _r	$V_{GE} = 15V, R_{G} = 10\Omega$	-	38	-	no
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	107	-	ns
Fall Time	t _f	Inductive Load	-	65	-	
		$I_C = 100A, V_{CC} = 520V$				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650 \text{V}, \ V_{GE} = 15 \text{V}$	FULL SQUARE			-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

• Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

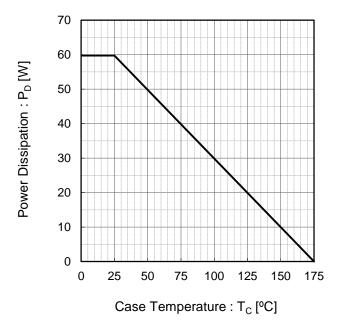
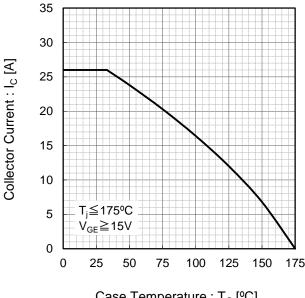
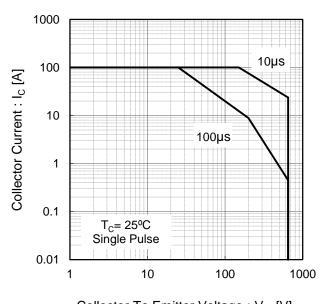


Fig.2 Collector Current vs. Case Temperature



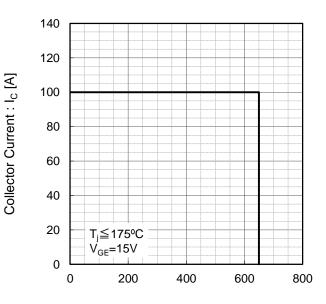
Case Temperature : T_C [°C]

Fig.3 Forward Bias Safe Operating Area



Collector To Emitter Voltage : $V_{CE}[V]$

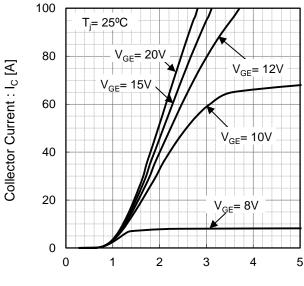
Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage : $V_{CE}[V]$

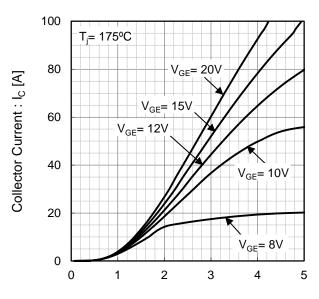
•Electrical Characteristic Curves

Fig.5 Typical Output Characteristics



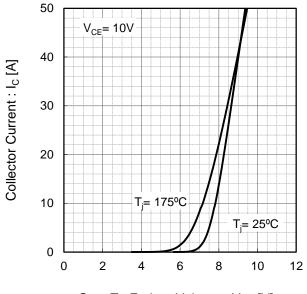
Collector To Emitter Voltage : $V_{CE}[V]$

Fig.6 Typical Output Characteristics



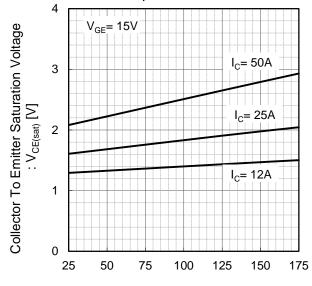
Collector To Emitter Voltage : V_{CE}[V]

Fig.7 Typical Transfer Characteristics



Gate To Emitter Voltage : $V_{GE}[V]$

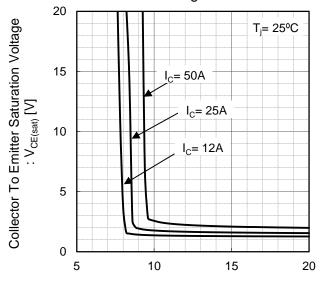
Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

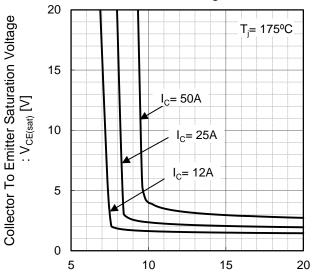
• Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V_{GE} [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage: V_{GE} [V]

Fig.11 Typical Switching Time vs. Collector Current

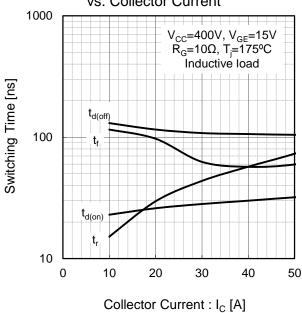
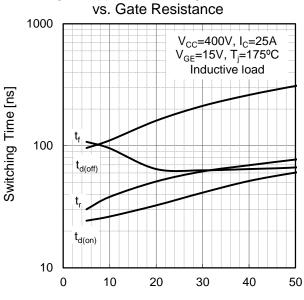


Fig.12 Typical Switching Time



Gate Resistance : $R_G[\Omega]$

• Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 E_{off} 0.1 V_{CC} =400V, V_{GE} =15V R_G=10 Ω , T_j=175°C Inductive load 0.01 0 10 30 40 20 50 Collector Current : I_C [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] E_{off} 1 0.1 V_{CC}=400V, I_C=25A V_{GE}=15V, T_j=175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V_{GE}=0V T_i=25°C 0.01 0.1 1 10 100

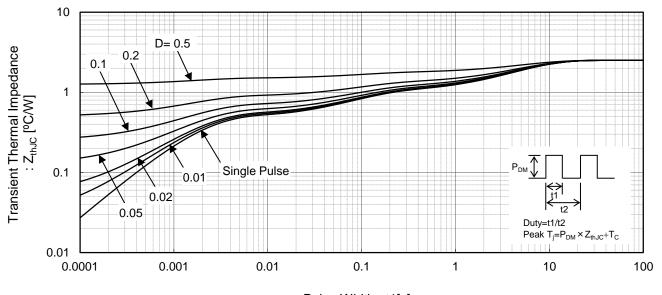
Collector To Emitter Voltage : V_{CE}[V]

Fig.16 Typical Gate Charge

15 V_{abs} 10 V_{cc} 10 V_{cc} V_{cc} V

•Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

●Inductive Load Switching Circuit and Waveform

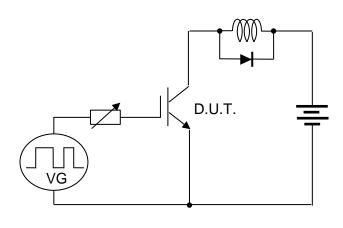


Fig.18 Inductive Load Circuit

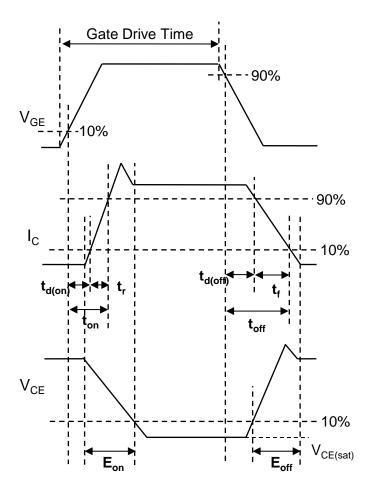


Fig.19 Inductive Load Waveform

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